

FORM PTO-1449	SERIAL NO. Not yet assigned	CASE NO. 10322/57 Client Ref. No. TF03009
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE Herewith	GROUP ART UNIT Not yet assigned
(use several sheets if necessary)		APPLICANT(S): Kuang-Chien Hsieh et al.

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.	
WZ	A3	K. L. Chang, G.W. Pickrell, D.E. Wohler, J.H. Epple, H.C. Lin, K.Y. Cheng and K.C. Hsieh, <i>Microstructure and Wet Oxidation of Low-Temperature-Grown Amorphous (Al/Ga,As)</i> , American Institute of Physics, Vol. 89 No. 1, pgs. 747-752, January 1, 2001.
	A4	J.J. Epple, K.L. Chang, C.F. Xu, G.W. Pickrell, K.Y. Chang, and K.C. Hsieh, <i>Formation of Highly Conductive Polycrystalline GaAs from Annealed Amorphous (Ga,As)</i> , American Institute of Physics, pgs. 5331-5336, May 1, 2003.
	A5	H.C. Lin, W.H. Wang, K.C. Hsieh and K.Y. Cheng, <i>Fabrication of 1.55μm VCSELs on Si Using Metallic Bonding</i> , Electronics Letters, Vol. 38 No. 11, May 23, 2002.
	A6	H.C. Lin, K.L. Chang, K.C. Hsieh, K.Y. Cheng, <i>Metallic Wafer Bonding for the Fabrication of Long-Wavelength Vertical-Cavity Surface-Emitting Lasers</i> , Journal of Applied Physics, Vol. 92 No. 7, pgs. 4132-4134, October 1, 2002.
	A7	H.C. Lin, K.L. Chang, G.W. Pickrell, K.C. Hsieh and K.Y. Cheng, <i>Low Temperature Wafer Bonding by Spin on Glass</i> , Journal of Vacuum Science & Technology B, Vol. 20 No. 2, pgs. 752-754, March/April 2002.
	A8	G.W. Pickrell, K.L. Chang, J.H. Epple, K.Y. Chang and K.C. Hsieh, <i>Protection of In_{0.25}Ga_{0.75}As/GaAs Structures During Lateral Oxidation Using an Amorphous InGaP Layer</i> , American Vacuum Society, Vol. 20 No. 3, pgs. 876-879, May/June 2002.
	A9	G.W. Pickrell, K.L. Chang, H.C. Lin, K.C. Hsieh and K.Y. Cheng, <i>Very-Low-Temperature Molecular Beam Epitaxial Growth of GaP/AlAs Heterostructures for Distributed Bragg Reflector Applications</i> , American Vacuum Society; pgs. 1536-1540, July/Aug. 2001.
	A10	G.W. Pickrell, H.C. Lin, K.L. Chang, K.C. Hsieh and K.Y. Cheng, <i>Fabrication of GaP/Al-Oxide Distributed Bragg Reflectors for the Visible Spectrum</i> , Applied Physics Letters, Vol. 78 No. 8, pgs. 1044-1046, February 19, 2001
	A11	Frank Shi, Scott MacLaren, Chaofeng Xu, K.Y. Cheng and K.C. Hsieh, <i>Hybrid-integrated GaAs/GaAs and InP/GaAs Semiconductors Through Wafer Bonding Technology: Interface Adhesion and Mechanical Strength</i> , American Institute of Physics, pgs. 5750-5756, May 1, 2003.
	A12	Frank F. Shi, Kuo-Lih Chang and Veronica I. Lai, <i>UltraWafer, Inc., A UIUC Semiconductor Start-up, Speeding Up What's Next</i> , pgs. 2-24,
	A13	D.E. Wohler, H.C. Lin, K.L. Chang, G.W. Pickrell, Jr., J.H. Epple, K.C. Hsieh, K.Y. Cheng, <i>Fabrication of a Substrate-Independent Aluminum Oxide-GaAs Distributed Bragg Reflector</i> , Applied Physics Letters, Vol. 75 No. 10, pgs. 1371-1373, September 6, 1999.

EXAMINER	DATE CONSIDERED
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

made of record. Copies of the listed documents required by 37 C.F.R. § 1.98(a)(2) are enclosed for the convenience of the Examiner.

The references now cited are the following:

OTHER ART – NON PATENT LITERATURE DOCUMENTS
L.J. Chou, K.C. Hsieh, D.E. Wohlert and K.Y. Cheng, <i>Formation of Amorphous Aluminum Oxide and Gallium Oxide on InP Substrates by Water Vapor Oxidation</i> , American Institute of Physics, pgs. 6932-6934, December 15, 1998.
L.J. Chou, K.C. Hsieh, A. Moy, D.E. Wohlert, G. Pickrell and K.Y. Cheng, <i>Improving the Al-Bearing Native-Oxide/GaAs Interface Formed by Wet Oxidation with a Thin GaP Barrier Layer</i> , American Institute of Physics, pgs. 2722-2724, May 25, 2003.
K. L. Chang, G.W. Pickrell, D.E. Wohlert, J.H. Eppler, H.C. Lin, K.Y. Cheng and K.C. Hsieh, <i>Microstructure and Wet Oxidation of Low-Temperature-Grown Amorphous (Al/Ga,As)</i> , American Institute of Physics, Vol. 89 No. 1, pgs. 747-752, January 1, 2001.
J.J. Eppler, K.L. Chang, C.F. Xu, G.W. Pickrell, K.Y. Chang, and K.C. Hsieh, <i>Formation of Highly Conductive Polycrystalline GaAs from Annealed Amorphous (Ga,As)</i> , American Institute of Physics, pgs. 5331-5336, May 1, 2003.
H.C. Lin, W.H. Wang, K.C. Hsieh and K.Y. Cheng, <i>Fabrication of 1.55μm VCSELs on Si Using Metallic Bonding</i> , Electronics Letters, Vol. 38 No. 11, May 23, 2002.
H.C. Lin, K.L. Chang, K.C. Hsieh, K.Y. Cheng, <i>Metallic Wafer Bonding for the Fabrication of Long-Wavelength Vertical-Cavity Surface-Emitting Lasers</i> , Journal of Applied Physics, Vol. 92 No. 7, pgs. 4132-4134, October 1, 2002.
H.C. Lin, K.L. Chang, G.W. Pickrell, K.C. Hsieh and K.Y. Cheng, <i>Low Temperature Wafer Bonding by Spin on Glass</i> , Journal of Vacuum Science & Technology B, Vol. 20 No. 2, pgs. 752-754, March/April 2002.
G.W. Pickrell, K.L. Chang, J.H. Eppler, K.Y. Chang and K.C. Hsieh, <i>Protection of In_{0.25}Ga_{0.75}As/GaAs Structures During Lateral Oxidation Using an Amorphous InGaP Layer</i> , American Vacuum Society, Vol. 20 No. 3, pgs. 876-879, May/June 2002.
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G.W. Pickrell, H.C. Lin, K.L. Chang, K.C. Hsieh and K.Y. Cheng; <i>Fabrication of GaP/Al-Oxide Distributed Bragg Reflectors for the Visible Spectrum</i> , Applied Physics Letters, Vol. 78 No. 8, pgs. 1044-1046, February 19, 2001
Frank Shi, Scott MacLaren, Chaofeng Xu, K.Y. Cheng and K.C. Hsieh, <i>Hybrid-integrated GaAs/GaAs and InP/GaAs Semiconductors Through Wafer Bonding Technology: Interface Adhesion and Mechanical Strength</i> ; American Institute of Physics, pgs. 5750-5756, May 1, 2003.
Frank F. Shi, Kuo-Lih Chang and Veronica I. Lai, <i>UltraWafer, Inc., A UIUC Semiconductor Start-up, Speeding Up What's Next</i> , pgs. 2-24,
D.E. Wohlert, H.C. Lin, K.L. Chang, G.W. Pickrell, Jr., J.H. Eppler, K.C. Hsieh, K.Y. Cheng, <i>Fabrication of a Substrate-Independent Aluminum Oxide-GaAs Distributed Bragg Reflector</i> , Applied Physics Letters, Vol. 75 No. 10, pgs. 1371-1373, September 6, 1999.